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AI  
conc.  
7. (Amended) The semiconductor nonvolatile storage element according to Claim 1 or 2:

wherein the ferroelectric layer is a layer of one material selected from a group consisting of  $\text{SrBi}_2\text{Ta}_2\text{O}_9$ ,  $\text{PbTiO}_3$ ,  $\text{PbZr}_x\text{Ti}_{1-x}\text{O}_3$ ,  $\text{Pb}_y\text{La}_{1-y}\text{Zr}_x\text{Ti}_{1-x}\text{O}_3$ ,  $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ ,  $\text{SrNbO}_7$ ,  $\text{Pb}_5\text{Ge}_3\text{O}_{11}$  and  $\text{Sr}_2\text{Ta}_x\text{Nb}_{1-x}\text{O}_7$ .

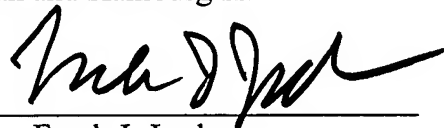
### REMARKS

This Preliminary Amendment is being submitted to avoid having a multiple dependent claim depend on another multiple dependent claim. It is respectfully requested that the first Office Action be directed to the application as amended herein.

Respectfully submitted,

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By



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Enc.

Appendix I (Amended claims with amendments indicated therein by brackets and underlining)

**APPENDIX I**

**AMENDED CLAIMS WITH AMENDMENTS INDICATED THEREIN  
BY BRACKETS AND UNDERLINING**

4. (Amended) The semiconductor nonvolatile storage element according to [any one of Claims 1 through 3] Claim 1 or 2:

wherein an area of the second conductor layer above the ferroelectric layer is made smaller than an area of the ferroelectric layer.

5. (Amended) The semiconductor nonvolatile storage element according to [any one of Claims 1 through 4] Claim 1 or 2:

wherein the second conductor layer is disposed above an element isolating region of the semiconductor substrate.

6. (Amended) The semiconductor nonvolatile storage element according to [any one of Claims 1 through 5] Claim 1 or 2:

wherein each of the first insulator layer and the second insulator thin film comprises a layer of one material or a layer laminated with two or more of materials selected from a group consisting of SiO<sub>2</sub> (silicon oxide), SiN (silicon nitride), Si<sub>3</sub>N<sub>4</sub> (silicon oxynitride), SiO<sub>2</sub>-SiN (ON film: silicon oxide - silicon nitride), SiO<sub>2</sub>-SiN-SiO<sub>2</sub> (ONO film: silicon oxide - silicon nitride - silicon oxide), Ta<sub>2</sub>O<sub>5</sub>,

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$\text{SrTiO}_3$ ,  $\text{TiO}_2$ ,  $(\text{Ba}, \text{Sr})\text{TiO}_3$ ,  $\text{Al}_2\text{O}_3$ ,  $\text{ZrO}_2$ ,  $\text{HfO}_2$ ,  $\text{Y}_2\text{O}_3$ ,  $\text{CeO}_2$ ,  $\text{CeZrO}_2$  and YSZ (yttrium oxide stabilized zirconium oxide).

7. (Amended) The semiconductor nonvolatile storage element according to [any one of Claims 1 through 6] Claim 1 or 2:

wherein the ferroelectric layer is a layer of one material selected from a group consisting of  $\text{SrBi}_2\text{Ta}_2\text{O}_9$ ,  $\text{PbTiO}_3$ ,  $\text{PbZr}_x\text{Ti}_{1-x}\text{O}_3$ ,  $\text{Pb}_y\text{La}_{1-y}\text{Zr}_x\text{Ti}_{1-x}\text{O}_3$ ,  $\text{Bi}_4\text{Ti}_3\text{O}_{12}$ ,  $\text{SrNbO}_7$ ,  $\text{Pb}_5\text{Ge}_3\text{O}_{11}$  and  $\text{Sr}_2\text{Ta}_x\text{Nb}_{1-x}\text{O}_7$ .